Ordering number:EN5985

N-Channel MOS Silicon FET

CPH3403

Ultrahigh-Speed Switching Applications

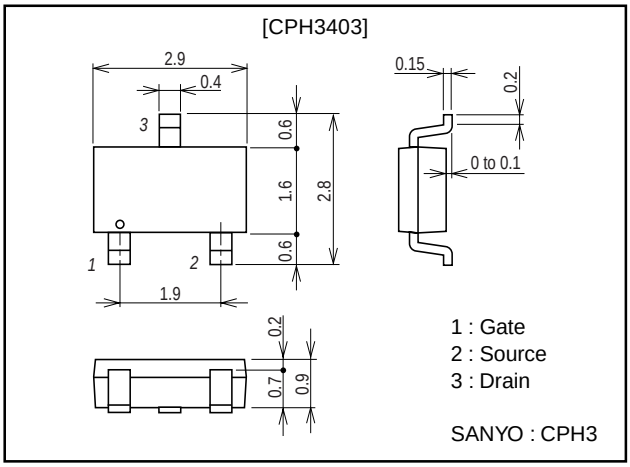
Features

- Low ON resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Package Dimensions

unit:mm

2152



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		20	V
Gate-to-Source Voltage	V_{GSS}		±12	V
Drain Current (DC)	I_D		2.2	A
Drain Current (pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	8.8	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (900mm²×0.8mm)	1.0	W
Channel Temperature	Tch		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V, V_{GS}=0			10	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=10V, I_D=1mA	0.4		1.3	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=1A	2.5	3.6		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}1$	I_D=1A, V_{GS}=4V		115	150	mΩ
	$R_{DS(on)}2$	I_D=0.5A, V_{GS}=2.5V		160	220	mΩ
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		170		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		90		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		43		pF

Marking : KC

Continued on next page.

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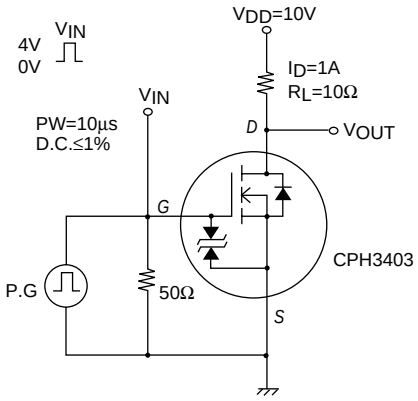
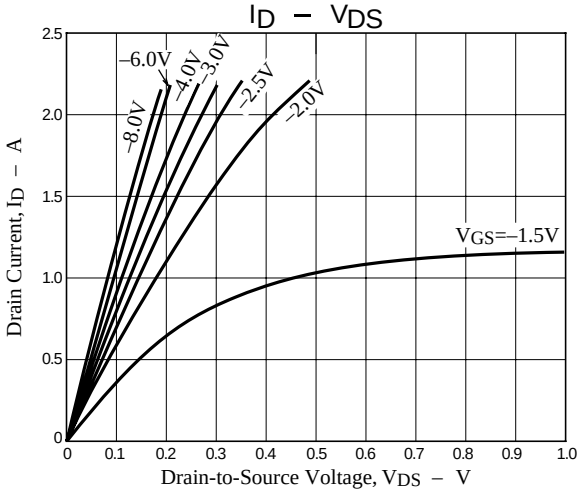
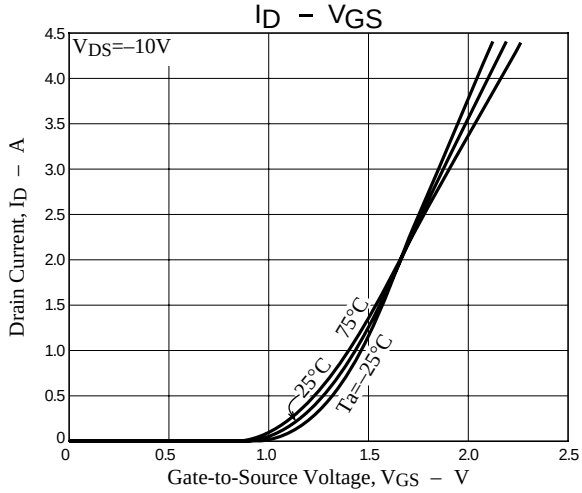
Continued from preceding page.

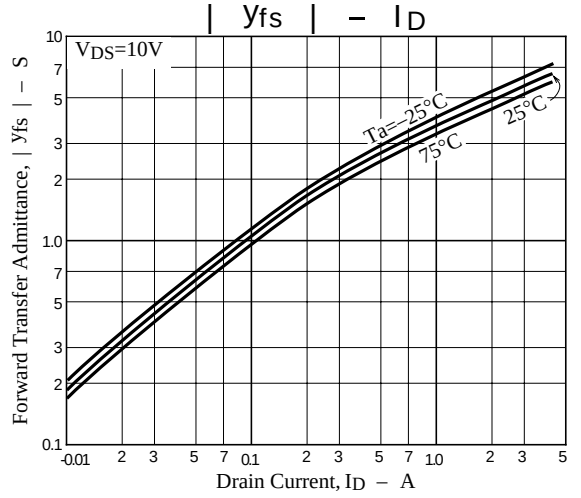
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		10		ns
Rise Time	t_r	See specified Test Circuit		20		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		36		ns
Fall Time	t_f	See specified Test Circuit		27		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=10V, I_D=2.2A		9.5		nC
Gate-to-Source Charge	Qgs	V_{DS}=10V, V_{GS}=10V, I_D=2.2A		1		nC
Gate-to-Drain "Miller" Charge	Qgd	V_{DS}=10V, V_{GS}=10V, I_D=2.2A		1.5		nC
Diode Forward Voltage	V_{SD}	I_S=2.2A, V_{GS}=0		1.0	1.2	V

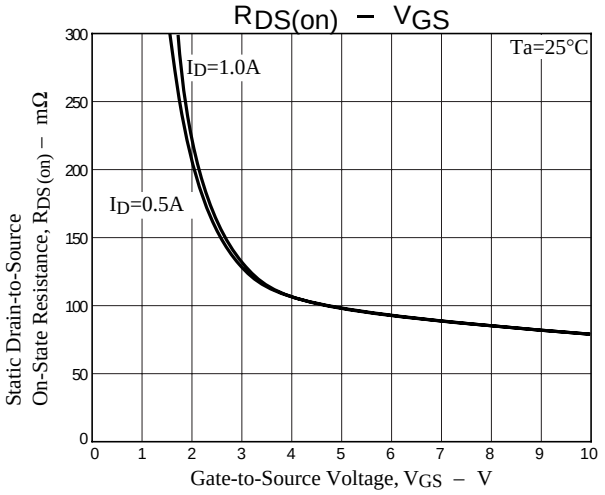
Switching Time Test Circuit

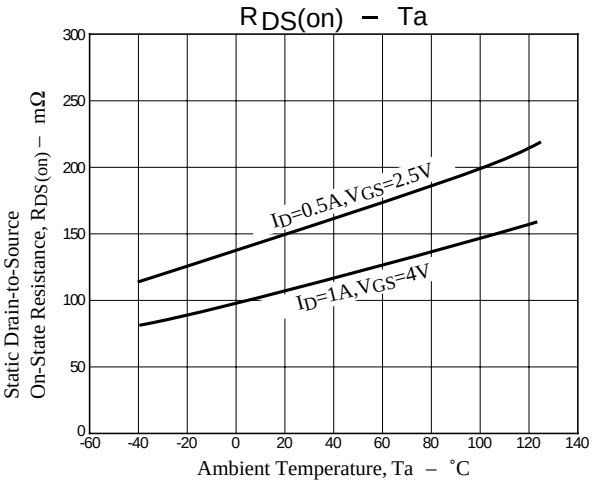


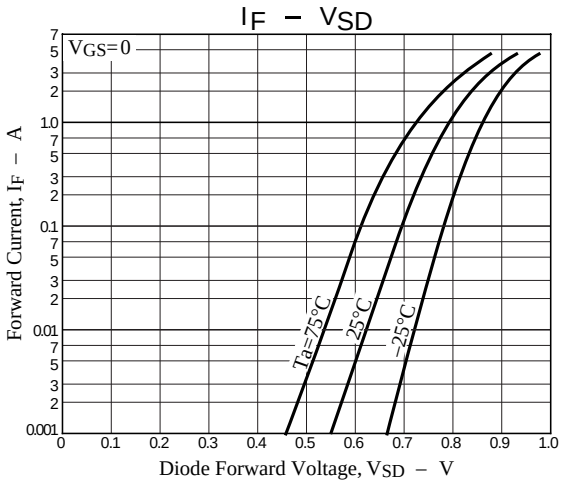


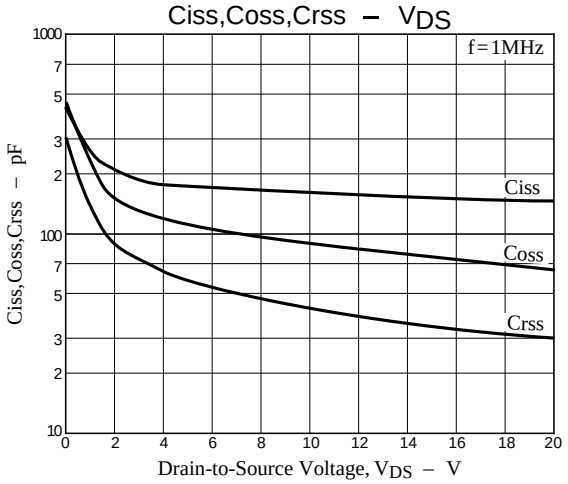


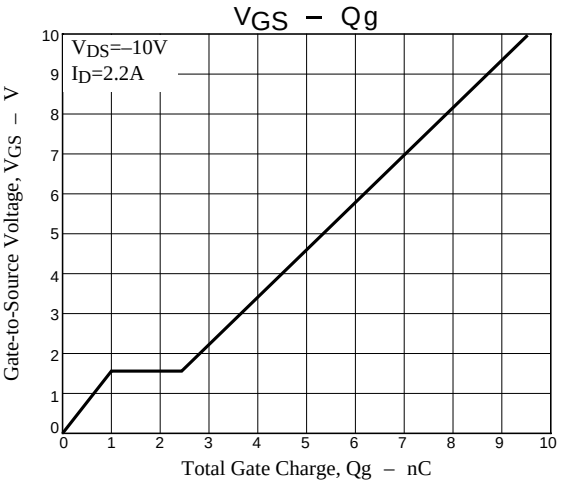


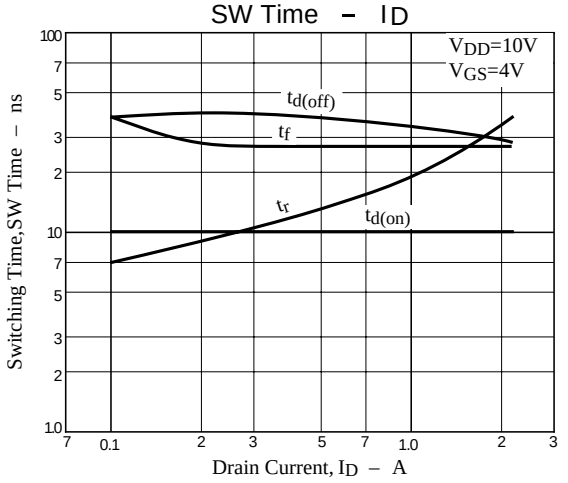


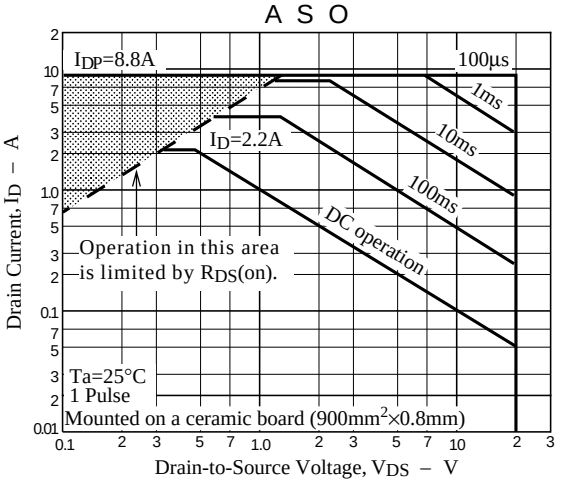

RDS(on) – Ta
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
ID=0.5A,VGS=2.5V
ID=1A,VGS=4V
Ambient Temperature, Ta – °C

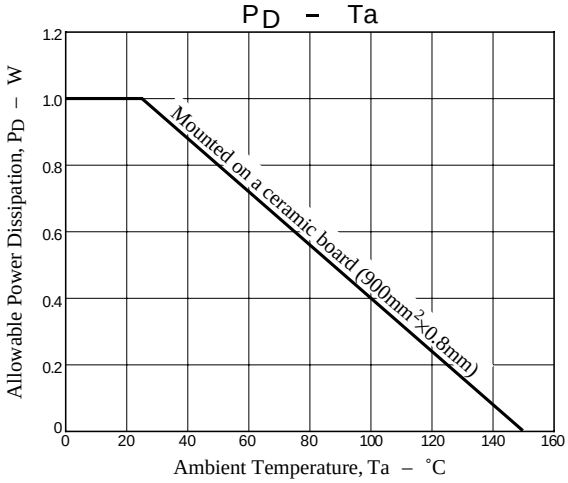

IF – VSD
VGS=0
Ta=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V


Ciss,Coss,Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss,Coss,Crss – pF
Drain-to-Source Voltage, VDS – V


VGS – Qg
VDS=–10V
ID=2.2A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC


SW Time – ID
VDD=10V
VGS=4V
td(off)
tf
tr
td(on)
Switching Time,SW Time – ns
Drain Current, ID – A


A S O
IDP=8.8A
100µs
1ms
10ms
100ms
DC operation
ID=2.2A
Operation in this area
is limited by RDS(on).
Ta=25°C
1 Pulse
Mounted on a ceramic board (900mm2×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V


PD – Ta
Mounted on a ceramic board (900mm2×0.8mm)
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C